

Application No.: 10/686,893 YAO-3990US3
Amendment Dated: February 27, 2007
Reply to Office Action of: October 27, 2006



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appln. No: 10/686,893
Applicants: Hidetoshi ISHIDA, et al.
Filed: October 16, 2003
Title: ETCHANT AND METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE USING THE SAME
TC/A.U.: 2823
Examiner: Q. Jefferson
Confirmation No.: 8582
Docket No.: YAO-3990US3

AMENDMENT UNDER 37 C.F.R. § 1.116

Expedited Procedure

Mail Stop AF

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Responsive to the Final Office Action dated **October 27, 2006**, please amend the above-identified application as follows:

- Amendments to the Specification** begin on page _____ of this paper.
- Amendments to the Claims** are reflected in the listing of claims which begins on page **2** of this paper.
- Amendments to the Drawings** begin on page _____ of this paper and include an attached replacement sheet(s).
- Amendments to the Abstract** are on page _____ of this paper. A clean version of the Abstract is on page _____ of this paper.
- Remarks/Arguments** begin on page **3** of this paper.